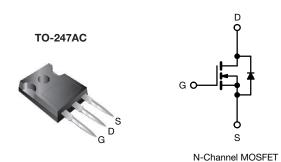
Vishay Siliconix

E Series Power MOSFET



PRODUCT SUMMARY				
V_{DS} (V) at T_J max.	850			
R _{DS(on)} typ. (Ω) at 25 °C	V _{GS} = 10 V 0.160			
Q _g max. (nC)	89			
Q _{gs} (nC)	15			
Q _{gd} (nC)	30			
Configuration	Single			

FEATURES

- Low figure-of-merit (FOM) Ron x Qa
- Low effective capacitance (Co(er))



Avalanche energy rated (UIS)

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE

APPLICATIONS

- · Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	SiHG24N80AE-GE3

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V _{DS}	800	V
Gate-source voltage			V_{GS}	± 30	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Continuous drain surrent (T = 150 °C)	V _{GS} at 10 V	T _C = 25 °C T _C = 100 °C	,	21	
Continuous drain current ($T_J = 150 ^{\circ}\text{C}$) V_{GS} at 10 V $T_{C} = 100 ^{\circ}\text{C}$		ID	13	Α	
Pulsed drain current a			I _{DM}	51	
Linear derating factor				1.7	W/°C
Single pulse avalanche energy b			E _{AS}	127	mJ
Maximum power dissipation			P _D	208	W
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +150	°C
Drain-source voltage slope $T_J = 125 ^{\circ}\text{C}$			1 / 11	70	1//
Reverse diode dv/dt d			dv/dt	34	V/ns
Soldering recommendations (peak temperature) c For 10 s			260	°C	

Notos

- a. Repetitive rating; pulse width limited by maximum junction temperature
- b. V_{DD} = 140 V, starting T_J = 25 °C, L = 28.2 mH, R_q = 25 Ω , I_{AS} = 3 A
- c. 1.6 mm from case
- d. $I_{SD} \le I_D$, di/dt = 100 A/ μ s, starting $T_J = 25$ °C



Vishay Siliconix

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	-	40	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	0.6	C/VV

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		^			•		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		800	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I _D = 1 mA	-	0.8	-	V/°C
Gate-source threshold voltage (N)	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = 250 μA	2	-	4	V
Coto pouros loskoro		,	$V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Gate-source leakage	I_{GSS}	,	$V_{GS} = \pm 30 \text{ V}$	-	-	± 1	μΑ
7		V _{DS} =	800 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 640 V	, V _{GS} = 0 V, T _J = 125 °C	-	-	10	μA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.160	0.184	Ω
Forward transconductance ^a	9 _{fs}	V _{DS}	= 30 V, I _D = 12 A	-	5.5	-	S
Dynamic							
Input capacitance	C _{iss}		V _{GS} = 0 V,	-	1836	-	
Output capacitance	C _{oss}	Ţ,	$V_{DS} = 100 \text{ V},$	-	65	-	1
Reverse transfer capacitance	C _{rss}	f = 1 MHz		-	5	-	pF
Effective output capacitance, energy related	C _{o(er)}			-	52	-	
Effective output capacitance, time related	C _{o(tr)}	V _{DS} = 0 \	$V_{DS} = 0 \text{ V to } 480 \text{ V}, V_{GS} = 0 \text{ V}$		338	-	
Total gate charge	Qg			-	59	89	
Gate-source charge	Q _{gs}	V _{GS} = 10 V	$I_D = 12 \text{ A}, V_{DS} = 640 \text{ V}$	-	15	-	nC
Gate-drain charge	Q _{gd}			-	30	-	
Turn-on delay time	t _{d(on)}			-	21	42	
Rise time	t _r	V _{DD} =	640 V, I _D = 12 A,	-	44	88	
Turn-off delay time	t _{d(off)}	V _{GS} =	$= 10 \text{ V}, \text{ R}_{\text{g}} = 9.1 \Omega$	-	29	58	ns
Fall time	t _f			-	51	102	
Gate input resistance	R_g	f = 1	MHz, open drain	0.2	0.5	1.1	Ω
Drain-Source Body Diode Characteristic	s						
Continuous source-drain diode current	Is	MOSFET symbol showing the integral reverse p - n junction diode		-	-	21	
Pulsed diode forward current	I _{SM}			-	-	51	A
Diode forward voltage	V _{SD}	T _J = 25 °C	C, I _S = 12 A, V _{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t _{rr}			-	476	952	ns
Reverse recovery charge	Q _{rr}		5 °C, I _F = I _S = 12 A,	-	7.8	15.6	μC
Reverse recovery current	I _{RRM}	di/dt = 100 A/μs, V _R = 25 V		_	26	_	Α



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

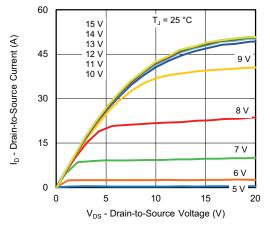


Fig. 1 - Typical Output Characteristics

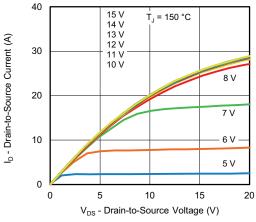


Fig. 2 - Typical Output Characteristics

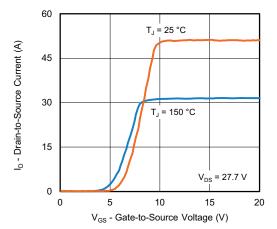


Fig. 3 - Typical Transfer Characteristics

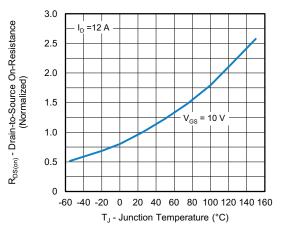


Fig. 4 - Normalized On-Resistance vs. Temperature

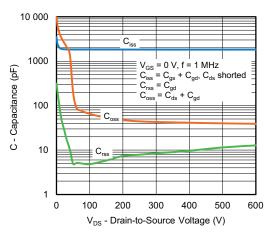


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

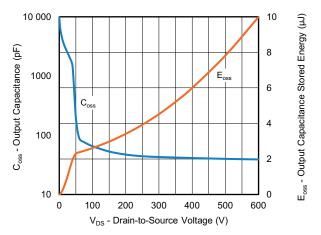


Fig. 6 - Coss and Eoss vs. VDS



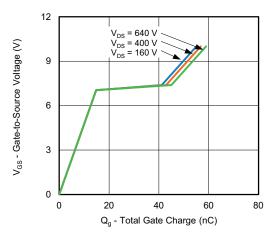


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

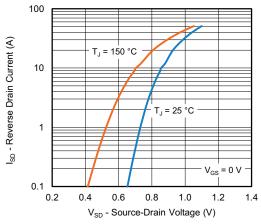


Fig. 8 - Typical Source-Drain Diode Forward Voltage

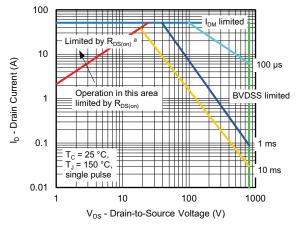


Fig. 9 - Maximum Safe Operating Area



a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

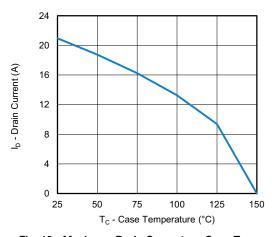


Fig. 10 - Maximum Drain Current vs. Case Temperature

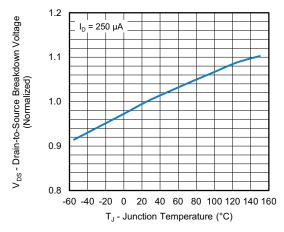


Fig. 11 - Temperature vs. Drain-to-Source Voltage



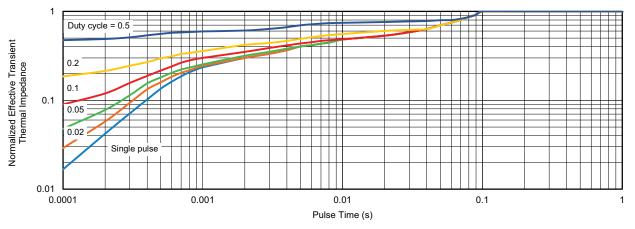


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

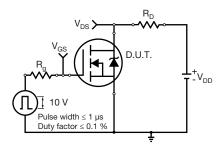


Fig. 13 - Switching Time Test Circuit

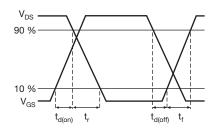


Fig. 14 - Switching Time Waveforms

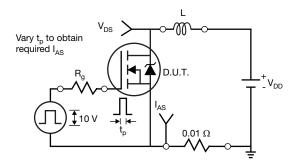


Fig. 15 - Unclamped Inductive Test Circuit

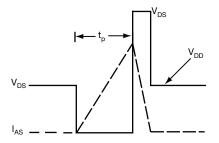


Fig. 16 - Unclamped Inductive Waveforms

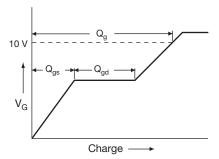


Fig. 17 - Basic Gate Charge Waveform

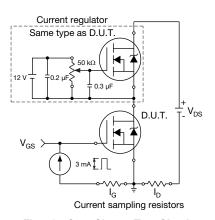
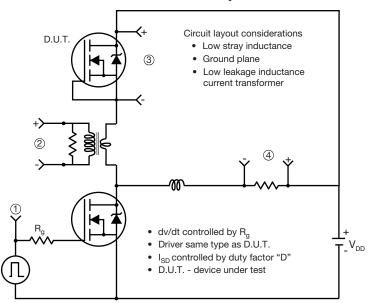


Fig. 18 - Gate Charge Test Circuit



Peak Diode Recovery dv/dt Test Circuit



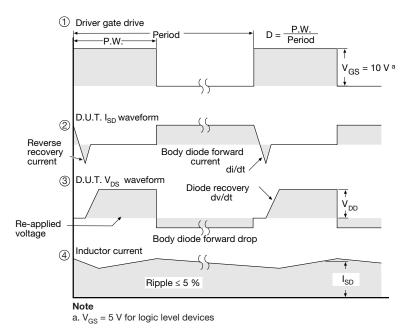


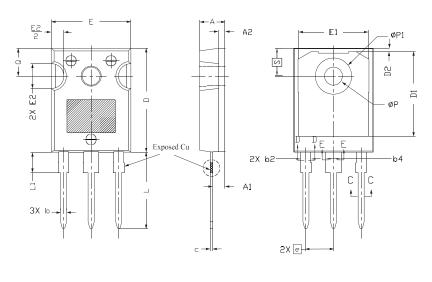
Fig. 19 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?92372.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D-D,E-E

	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES	
Α	4.83	5.02	5.21		
A1	2.29	2.41	2.55		
A2	1.17	1.27	1.37		
b	1.12	1.20	1.33		
b1	1.12	1.20	1.28		
b2	1.91	2.00	2.39	6	
b3	1.91	2.00	2.34		
b4	2.87	3.00	3.22	6, 8	
b5	2.87	3.00	3.18		
С	0.40	0.50	0.60	6	
c1	0.40	0.50	0.56		
D	20.40	20.55	20.70	4	

	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES	
D1	16.46	16.76	17.06	5	
D2	0.56	0.66	0.76		
Е	15.50	15.70	15.87	4	
E1	13.46	14.02	14.16	5	
E2	4.52	4.91	5.49	3	
е		5.46 BSC			
L	14.90	15.15	15.40		
L1	3.96	4.06	4.16	6	
ØΡ	3.56	3.61	3.65	7	
Ø P1	7.19 ref.				
Q	5.31	5.50	5.69		
S		5.51 BSC			

Notes

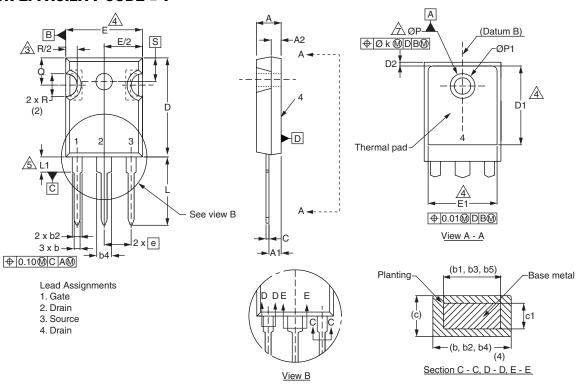
- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



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VERSION 2: FACILITY CODE = Y



	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	0.254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

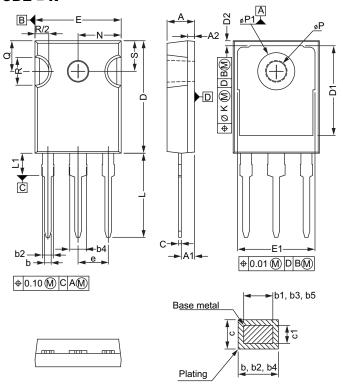
Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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